

Title (en)  
OPTOELECTRONIC SEMICONDUCTOR COMPONENT

Title (de)  
OPTOELEKTRONISCHES HALBLEITERBAUELEMENT

Title (fr)  
COMPOSANT SEMI-CONDUCTEUR OPTOÉLECTRONIQUE

Publication  
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Application  
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Abstract (en)  
[origin: WO2010081754A1] An optoelectronic semiconductor component is disclosed, comprising an active layer (4) suitable for the emission of radiation, enclosed by cover layers (3a, 3b), wherein the cover layers (3a, 3b) and/or the active layer (4) comprises an indium-containing phosphide compound semiconductor material and the phosphide compound semiconductor material contains at least one of the elements Sb or Bi as additional element of the V. main group. Furthermore, an optoelectronic semiconductor component with an active layer (4) suitable for emission of radiation is disclosed, wherein the active layer comprises an indium-containing nitride compound semiconductor material and the nitride compound semiconductor material of the active layer (4) contains at least one of the elements As, Sb or Bi as additional element of the V. main group.

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